In the Claims:

Please amend the claims as follows:

- 1. (Previously presented) An alcohol sensor utilizing a work function measurement principle comprising at least one gas-sensitive field-effect transistor which comprises at least one substrate having source and drain areas and at least one gate electrode located at a distance from a gate region between the source and drain areas, said gate electrode being associated with a gas-sensitive layer comprising a polymer or an inorganic metal oxide and wherein the layer is applied separately to the substrate such that it is substantially opposite a gate region of the field-effect transistor thereby forming a gap there between.
- 2. (Previously presented) The alcohol sensor according to claim 1, wherein the gas-sensitive layer comprises a polymer and is selected from the group consisting of polysiloxane [[or]] and a polysilsesquioxane derivative.
 - 3. (Cancelled)
- 4. (Original) The alcohol sensor according to claim 1, wherein the metal oxide is scandium oxide (Sc_2O_3).

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- 5. (Original) The alcohol sensor according to claim 1, further comprising an electrical heater.
- 6. (Original) The alcohol sensor according to claim 1, having an operating temperature in the range of between about room temperature and above 60°C.
- 7. (Original) The alcohol sensor according to claim 1, further comprising a plurality of different gas-sensitive layers.
- 8. (Original) The alcohol sensor according to claim 7, wherein a gas-sensitive layer is alcohol-sensitive and moisture-sensitive.
- 9. (Original) The alcohol sensor according to claim 8, wherein the moisture effects of the alcohol-sensitive layer are compensated for by means of the essentially moisture-sensitive layer.
- 10. (Original) The alcohol sensor according to claim 1, further comprising a gas-insensitive transistor for compensating for temperature effects.
- 11. (New) An alcohol sensor utilizing a work function measurement principle comprising at least one gas-sensitive field-effect transistor which comprises at least one substrate

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having source and drain areas and at least one gate electrode located at a distance from a gate region between the source and drain areas, said gate electrode being associated with a gassensitive layer comprising a polymer or an inorganic metal oxide and wherein the layer is applied separately to the substrate such that it is substantially opposite a gate region of the field-effect transistor thereby forming a gap there between, wherein the gas-sensitive layer comprises a polymer and is selected from the group consisting of polysiloxane [[or]] and a polysilsesquioxane derivative, wherein the polysilsesquioxane derivative is polycyclopentylsilsesquioxane.

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